

## Particle Statistics in Synchrotron Powder Diffraction

Takashi IDA\*, Taishi GOTO, Akihisa OYA, Hisashi HIBINO  
CRL, Nagoya Institute of Technology, Asahigaoka, Gifu 507-0071, Japan

### Introduction

We have recently developed a new analytical method to evaluate the statistical variance of measured diffraction intensity caused by the finite number of crystallites in crystalline powder specimens [1]. It has been found that the effective crystallite diameters over 5  $\mu\text{m}$  can be evaluated by statistical analysis of diffraction intensity data collected by stepwise rotation of a flat powder specimen with a laboratory Bragg-Brentano powder diffractometer, while the measurable size achieved by conventional line broadening analysis is limited within the range from 5 nm to 200 nm. However, it is also suggested that measurement of the intermediate crystallite size ranging from 200 nm to 3  $\mu\text{m}$  is practically impossible by using a laboratory diffractometer.

Use of synchrotron x-ray may expand the sensitivity of the crystallite size evaluation by the spinner scan measurement to smaller size, because smaller focal size is expected for synchrotron x-ray source. In this study, we have examined the effect of particle statistics on diffraction intensity data measured with the high-resolution powder diffractometer on the beamline BL-4B2 at KEK-PF.

### Experimental

Step-scan diffraction intensity data about the rotation angle of a Si powder specimen (NIST SRM640c) were collected. The effective diameter of the Si powder evaluated by SEM image analysis was 5.6  $\mu\text{m}$ .

Symmetric reflection mode was applied for the diffraction measurement. The cross section of the incident beam was limited with entrance slits of 1 mm in height and 10 mm in width. The calibrated peak wavelength of the x-ray was  $\lambda = 0.1208568(4)$  nm.

### Results and Discussions

The effective number of diffracting crystallites,  $n_{\text{eff}}$ , is calculated by  $n_{\text{eff}} = I^2 / (\Delta I_{\text{particle}})^2$ , where  $I$  is the mean intensity and  $(\Delta I_{\text{particle}})^2$  is the variance caused by particle statistics, which is evaluated by subtraction of variance caused by counting statistics from observed variance [2].

The theory proposed by Alexander et al. [2] suggests that  $n_{\text{eff}}$  is proportional to the effective multiplicity of reflection  $m_{\text{eff}}$  and also the cosecant of the Bragg angle  $\theta$ , when the crystallites are randomly oriented. Figure 1 shows the values of  $n_{\text{eff}} \sin \theta$  evaluated by the analysis of the spinner scan data measured on BL-4B2 and the known multiplicity  $m_{\text{eff}}$  of Si reflections. It has been found that the behavior of the observed values of  $n_{\text{eff}} \sin \theta$

and  $m_{\text{eff}}$  are well corresponded, but systematic deviation depending on the diffraction angle  $2\theta$  is also detected.

A similar plot for the data collected with a usual laboratory diffractometer (Rigaku RAD-2C) is shown in Fig. 2. The effective number of crystallites in powder diffraction measurement on BL-4B2 is roughly 1/20 of that measured with the laboratory diffractometer. It means that the effect of particle statistics in powder diffraction measurement on BL-4B2 will be more pronounced, unless continuous rotation of specimen is applied. Since  $n_{\text{eff}}$  is inversely proportional to the particle volume, it is also suggested that the measurable crystallite size in diameter will become 1/3 by applying the BL-4B2 diffractometer, as compared with a laboratory powder diffractometer.

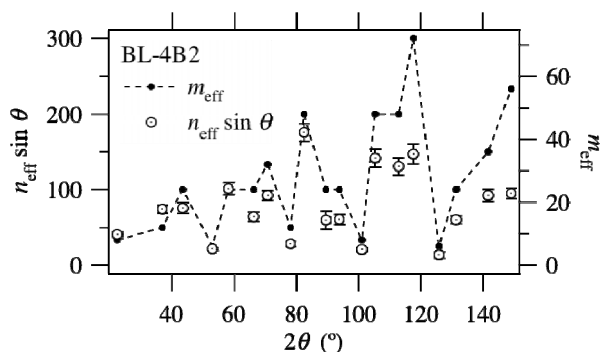


Fig. 1 Product of the effective number  $n_{\text{eff}}$  by  $\sin \theta$  (open circles) and the known multiplicity of reflection  $m_{\text{eff}}$  for Si (dots connected with broken lines).

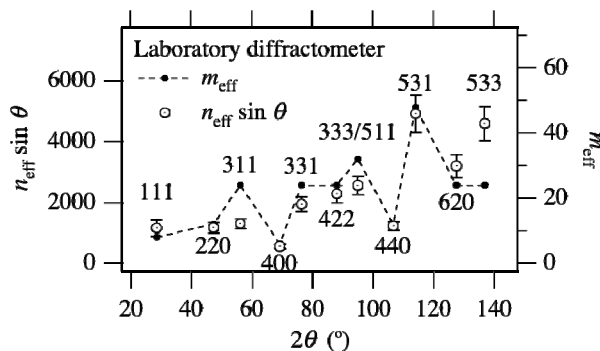


Fig. 2 Plot similar to Fig. 1, drawn with the data collected with a laboratory diffractometer.

### References

- [1] T. Ida et al., J. Appl. Cryst. (in press).
- [2] L. Alexander et al., J. Appl. Phys. 19, 742 (1948).

\* ida.takashi@nitech.ac.jp